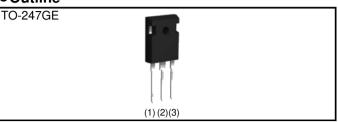


RGWS60TS65D 650V 30A Field Stop Trench IGBT

V _{CES}	650V
Ι _{C (100°C)}	30A
V _{CE(sat) (Typ.)}	1.6V
P _D	156W

Outline



Features

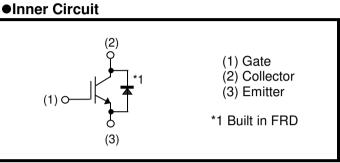
- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Built in Very Fast & Soft Recovery FRD
- 5) Pb free Lead Plating ; RoHS Compliant

Application

PFC

Solar converters

Mid to high switching frequency converters



Packaging Specifications

	Packaging	Tube
	Reel Size (mm)	-
Tuno	Tape Width (mm)	-
Туре	Basic Ordering Unit (pcs)	600
	Packing Code	C13
	Marking	RGWS60TS65D

•Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Paramet	ter	Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	650	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	$T_{\rm C} = 25^{\circ}{\rm C}$	Ι _C	51	Α
Collector Current	$T_{\rm C} = 100^{\circ}{\rm C}$	Ι _C	32	Α
Pulsed Collector Current		I _{CP} ^{*1}	90	Α
Diode Forward Current	$T_{\rm C} = 25^{\circ}{\rm C}$	١ _F	23	Α
Diode Forward Current	$T_{\rm C} = 100^{\circ}{\rm C}$	١ _F	13	A
Diode Pulsed Forward Current		I _{FP} ^{*1}	60	Α
Power Dissipation	$T_{\rm C} = 25^{\circ}{\rm C}$	P _D	156	W
Power Dissipation	$T_{\rm C} = 100^{\circ}{\rm C}$	P _D	78	W
Operating Junction Temperature		Tj	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

*1 Pulse width limited by $T_{jmax.}$

Thermal Resistance

Parameter	Symbol	Values			Unit
Farameter	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	0.96	°C/W
Thermal Resistance Diode Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	2.88	°C/W

•IGBT Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol Conditions -		Values			Unit
Farameter			Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{\rm C}$ = 10µA, $V_{\rm GE}$ = 0V	650	-	-	V
Collector Cut - off Current	I _{CES}	$V_{CE} = 650V, V_{GE} = 0V$	-	-	10	μA
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{\text{GE(th)}}$	V _{CE} = 5V, I _C = 13.3mA	5.0	6.0	7.0	V
Collector - Emitter Saturation Voltage	V _{CE(sat)}	$I_{C} = 30A, V_{GE} = 15V,$ $T_{j} = 25^{\circ}C$ $T_{j} = 175^{\circ}C$	-	1.6 2.0	2.0 -	V

●IGBT Electrical Characteris	stics (at T	i = 25°C unless otherwis	se specified)

Deverseter	Cumbal Canditiana	Conditions	Values				
Parameter	Symbol Conditions		Min.	Тур.	Max.	Unit	
Input Capacitance	C _{ies}	$V_{CE} = 30V,$	-	1680	-		
Output Capacitance	C _{oes}	$V_{GE} = 0V,$	-	47	-	pF	
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	31	-		
Total Gate Charge	Qg	V _{CE} = 400V,	-	58	-		
Gate - Emitter Charge	Q _{ge}	I _C = 30A,	-	12	-	nC	
Gate - Collector Charge	Q_{gc}	V _{GE} = 15V	-	24	-		
Turn - on Delay Time	t _{d(on)}		-	32	-		
Rise Time	t _r	$I_{C} = 30A, V_{CC} = 400V,$ $V_{GE} = 15V, R_{G} = 10\Omega,$	-	12	-	ns	
Turn - off Delay Time	t _{d(off)}	$T_i = 25^{\circ}C$	-	91	-		
Fall Time	t _f	Inductive Load	-	46	-		
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	0.50	-	ml	
Turn - off Switching Loss	E _{off}		-	0.45	-	mJ	
Turn - on Delay Time	t _{d(on)}		-	31	-		
Rise Time	t _r	$I_{\rm C} = 30$ A, $V_{\rm CC} = 400$ V, $V_{\rm GE} = 15$ V, $R_{\rm G} = 10$ Ω,	-	13	-	n 0	
Turn - off Delay Time	t _{d(off)}	$V_{GE} = 175^{\circ}, H_{G} = 1002,$ $T_{i} = 175^{\circ}C$	-	101	-	ns	
Fall Time	t _f	Inductive Load	-	74	-		
Turn - on Switching Loss	E _{on}	*E _{on} include diode reverse recovery	-	0.51	-	mJ	
Turn - off Switching Loss	E _{off}		-	0.56	-	IIIJ	
Reverse Bias Safe Operating Area	RBSOA	$I_{C} = 90A, V_{CC} = 520V$ $V_{P} = 650V, V_{GE} = 15V$ $R_{G} = 100\Omega, T_{j} = 175^{\circ}C$	FU	ILL SQUA	RE	-	

•FRD Electrical Characteristics (at $T_j = 25^{\circ}C$ unless otherwise specified)

Deremeter	C: unable of		Values			
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
		I _F = 10A,				
Diode Forward Voltage	V_{F}	T _j = 25°C	-	1.45	1.9	V
		T _j = 175°C	-	1.4	-	
Diode Reverse Recovery Time	t _{rr}		-	88	-	ns
Diode Peak Reverse Recovery Current	I _{rr}	I _F = 10A, V _{CC} = 400V,	-	5.9	-	A
Diode Reverse Recovery Charge	Q _{rr}	di _F /dt = 200A/µs, T _j = 25°C	-	0.28	-	μC
Diode Reverse Recovery Energy	E _{rr}		-	17.6	-	μJ
Diode Reverse Recovery Time	t _{rr}	$\begin{split} I_{F} &= 10 \text{A}, \\ V_{CC} &= 400 \text{V}, \\ di_{F}/dt &= 200 \text{A}/\mu \text{s}, \\ T_{j} &= 175^{\circ}\text{C} \end{split}$	-	105	-	ns
Diode Peak Reverse Recovery Current	I _{rr}		-	6.9	-	A
Diode Reverse Recovery Charge	Q _{rr}		-	0.42	-	μC
Diode Reverse Recovery Energy	E _{rr}		-	28.8	-	μJ

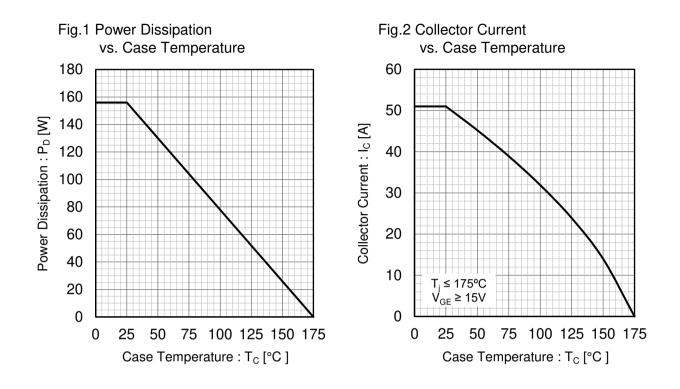
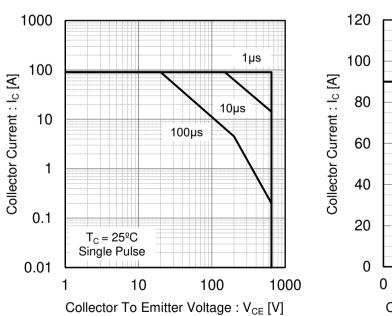
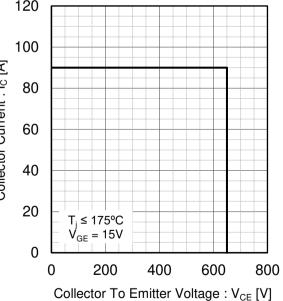


Fig.3 Forward Bias Safe Operating Area

Fig.4 Reverse Bias Safe Operating Area





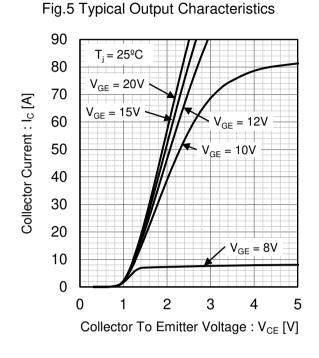


Fig.6 Typical Output Characteristics

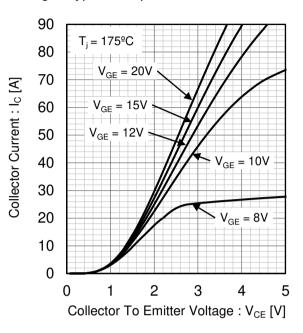
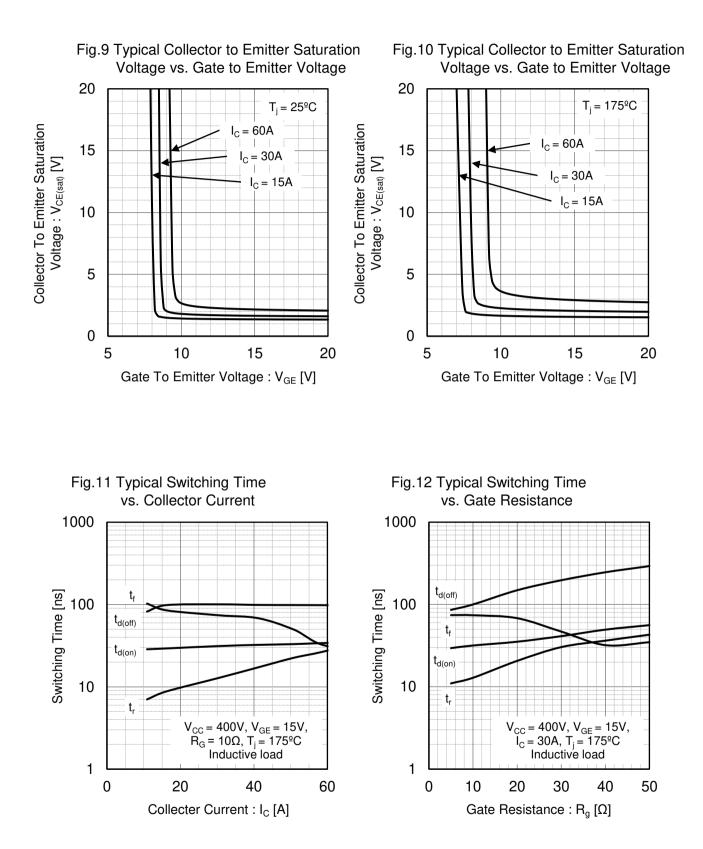
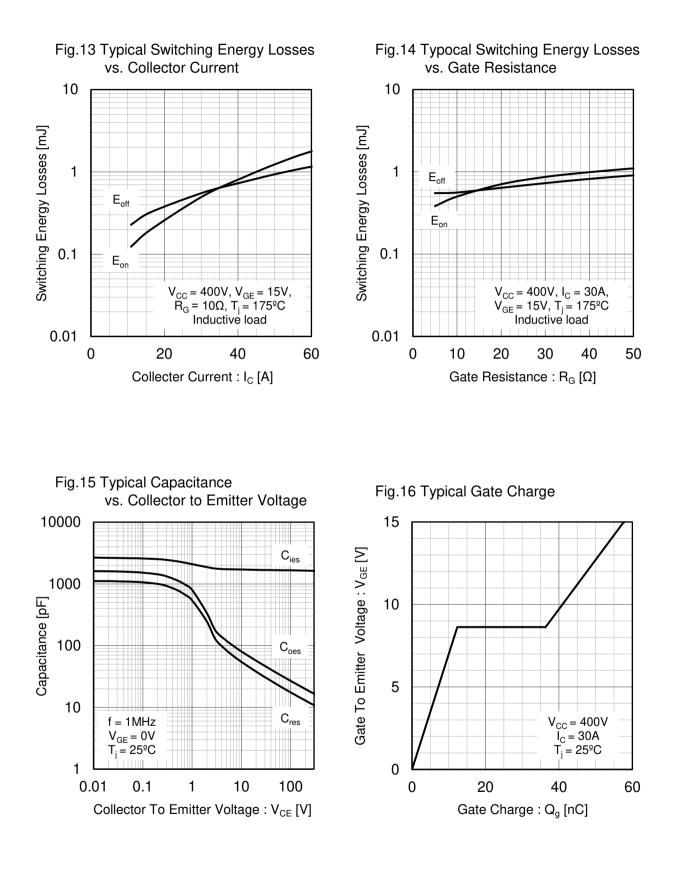


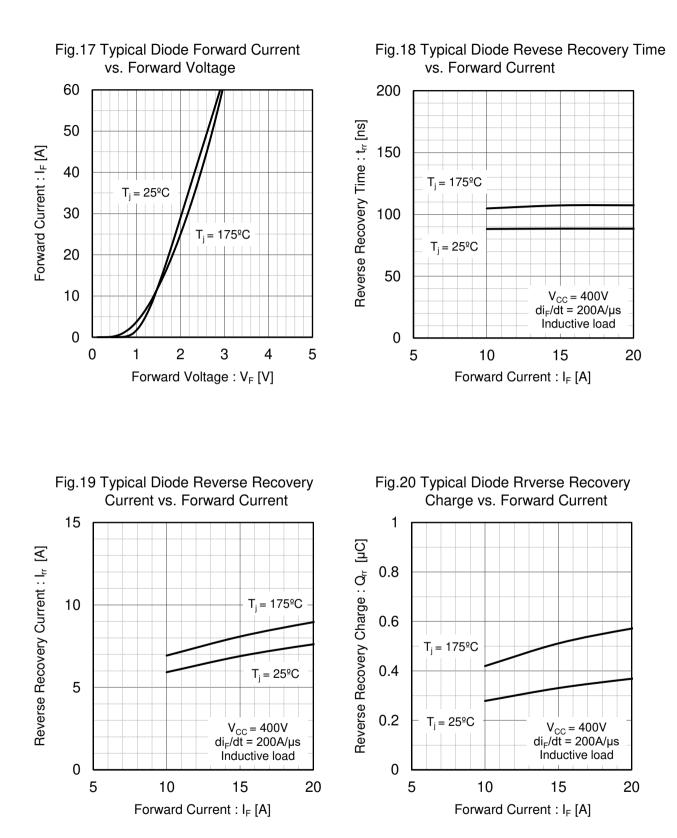
Fig.8 Typical Collector to Emitter Saturation Fig.7 Typical Transfer Characteristics Voltage vs. Junction Temperature 4 60 $V_{GE} = 15V$ $V_{CE} = 10V$ 50 Collector To Emitter Saturation $I_{\rm C} = 60 {\rm A}$ Collector Current : I_c [A] 3 Voltage : V_{CE(sat)} [V] 40 $I_{\rm C} = 30A$ 2 30 20 $I_{\rm C} = 15A$ 1 $T_{i} = 175^{\circ}C$ 10 $T_i = 25^{\circ}C$ 0 0 50 75 6 25 100 125 150 175 0 2 4 8 10 12

Gate To Emitter Voltage : V_{GE} [V]

Junction Temperature : T_i [°C]







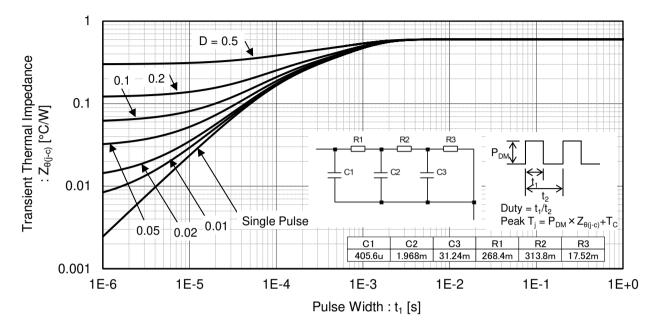
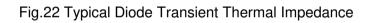
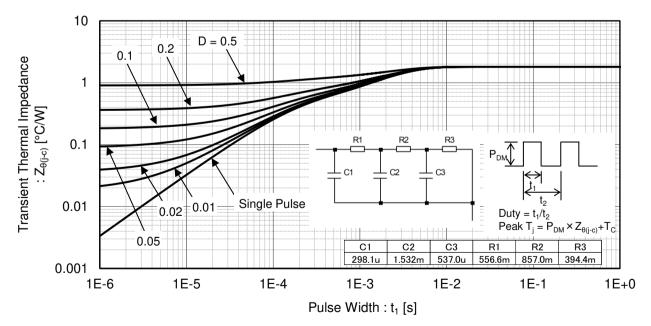


Fig.21 Typical IGBT Transient Thermal Impedance





Inductive Load Switching Circuit and Waveform

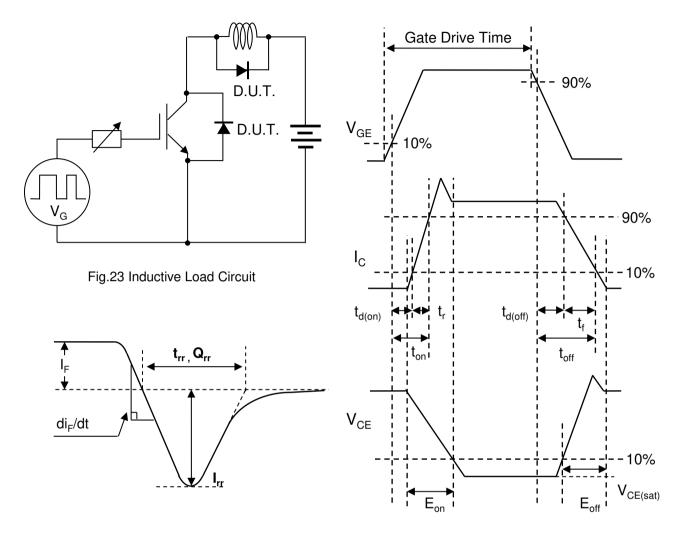


Fig.25 Diode Reverse Recovery Waveform

Fig.24 Inductive Load Waveform

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